



DESCRIPTION:

The Central Semiconductor CMPD7000E is an Enhanced version of the CMPD7000 Dual, Series Configuration, Ultra-High Speed Switching Diode. This device is manufactured by the epitaxial planar process, in an epoxy molded surface mount SOT-23 package, designed for high speed switching applications.

MARKING CODE: C5CE

FEATURED ENHANCED SPECIFICATIONS:

- ◆ BV_R from 100V min to 120V min.
- ♦ V_F from 1.1V max to 1.0V max.

		SYMBOL		UNITS
٠	Peak Repetitive Reverse Voltage	V _{RRM}	120	v
	Average Forward Current	ΙO	200	mA
	Peak Forward Current	IFM	500	mA
	Power Dissipation	PD	350	mW
	Operating and Storage			
	Junction Temperature	T _J ,T _{stg}	-65 to +150	°C
	Thermal Resistance	Θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

	SYMBOL	TEST CONDITIONS	MIN	ТҮР	МАХ	UNITS
٠	BV _R	Ι _R =100μΑ	120	150		v
	I _R	V _R =50V			300	nA
	I _R	V _R =50V, T _A =125°C			100	μA
	I _R	V _R =100V			500	nA
٠	V _F	I _F =1.0mA	0.55	0.59	0.65	v
٠	V _F	I _F =10mA	0.67	0.72	0.77	v
٠	V _F	I _F =100mA	0.85	0.91	1.0	v
	CT	V _R =0, f=1 MHz			1.5	pF
	t _{rr}	$I_R=I_F=10$ mA, R _L =100 Ω , Rec. to 1.0mA		2.0	4.0	ns

Enhanced Specification

R1 (13-November 2002)

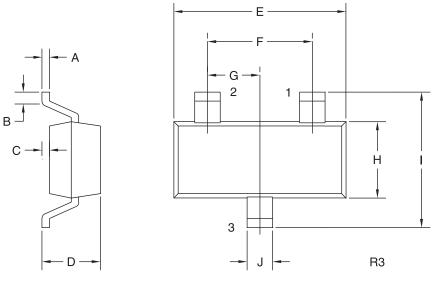
MAXIMUM RATINGS (TA=25°C)

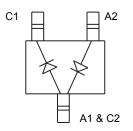


CMPD7000E

ENHANCED SPECIFICATION SURFACE MOUNT DUAL PAIR OF SERIES CONFIGURED SILICON SWITCHING DIODES

SOT-23 CASE - MECHANICAL OUTLINE





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DIMENSIONS INCHES MILLIMETERS SYMBOL MIN MAX MIN MAX А 0.003 0.007 0.08 0.18 В 0.006 0.15 --С 0.005 0.13 --0.89 D 0.035 0.043 1.09 0.110 0.120 2.80 3.05 Е F 0.075 1.90 G 0.037 0.95 0.047 0.055 Н 1.19 1.40 2.10 2.49 0.35 0.50 I 0.083 0.098 0.014 0.020 J

SOT-23 (REV: R3)

R1 (13-November 2002)